

Lecture 13: Film Deposition III

- Lecture Topics:
  - ↳ Film Deposition
    - Evaporation
    - Sputtering
    - Chemical Vapor Deposition
    - CVD Reactions
  - Epitaxial Growth
  - Atomic Layer Deposition (ALD)
- Last Time:
- Going through Module

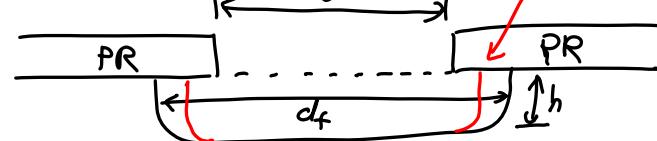
Etching

Two important metrics:

- ① Anisotropy
- ② Selectivity

① Anisotropy -

(a) Isotropic Etching: (most wet etches)



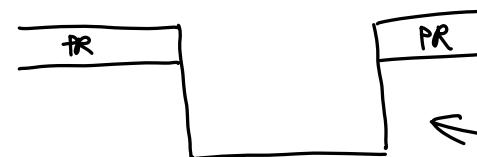
If 100% isotropic:  $d_f = d + 2h$

Define.  $B = d_f - d$  (total undercut)

If  $B = 2h \Rightarrow$  isotropic

(b) Partially Isotropic: (most dry etches, e.g., plasma etching)

$$\star \quad B < 2h$$

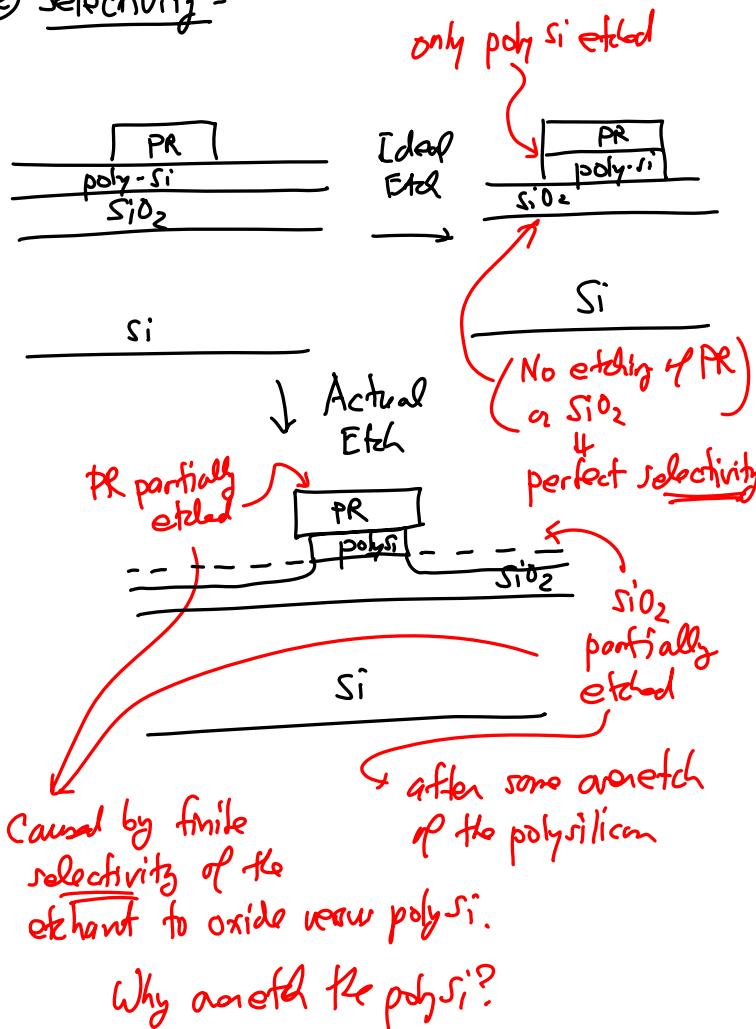
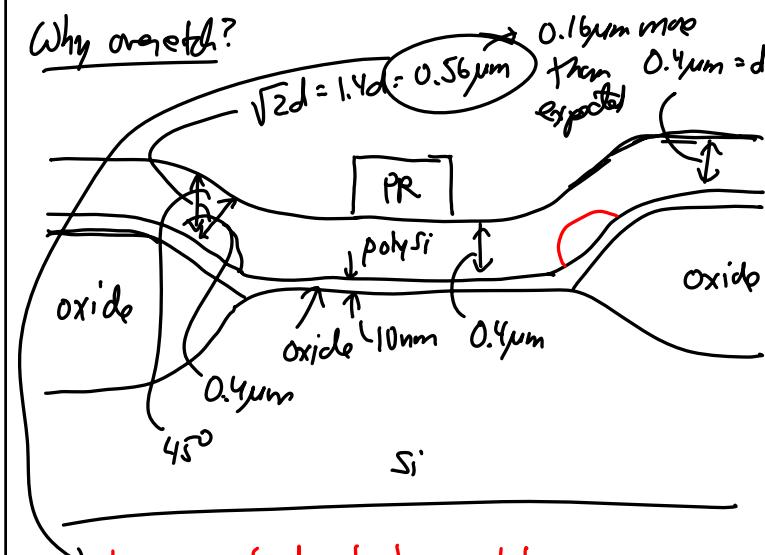


Degree of Anisotropy. (definition)

$$A_f = 1 - \frac{B}{2h} = 0 \text{ if } 100\% \text{ isotropic}$$

$$0 < A_f \leq 1 \quad \text{anisotropic}$$

over  $\rightarrow$

Lecture 13c: Film Deposition III(2) Selectivity -Why overetch?

↓  
Thus, must overetch by at least 40%:  
40% overetch →  $(0.4)(0.4) = 0.16\mu\text{m}$  polySi  
= ??? oxide